FCI-InGaAs-XXX-LCER

High Speed InGaAs Photodiodes Mounted on Ceramic Packages w/Leads

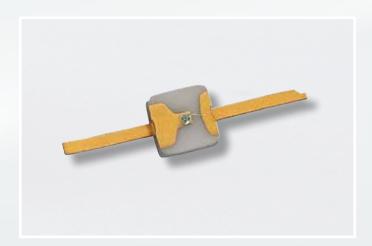
FCI-InGaAs-XXX-LCER with active area sizes of 75 μ m, 120 μ m, 300 μ m, 400 µm and 500 µm are part of OSI Optoelectronics's high speed IR sensitive photodiodes mounted on gull wing ceramic substrates. The chips can be epoxy/eutectic mounted onto the ceramic substrate.

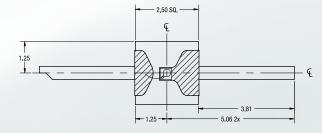
APPLICATIONS

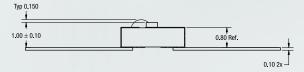
- · High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitoring
- Instrumentation

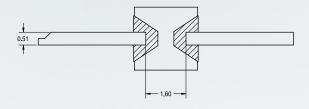
FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm









Notes:

- · All units in millimeters.
- All devices are mounted with low out gassing conductive epoxy with tolerance of ±25µm. Eutectic mounting is also available upon request.

Absolute Maximum Ratings											
PARAMETERS	SYMBOL	MIN	MAX	UNITS							
Storage Temperature	T _{stg}	-40	+85	°C							
Operating Temperature	T _{op}	0	+70	°C							
Soldering Temperature	T _{sld}		+260	°C							

Electro-Optical Characteristics T _A =2													23°C					
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-75LCER		FCI-InGaAs-120LCER		FCI-InGaAs-300LCER		FCI-InGaAs-400LCER			FCI-InGaAs-500LCER			UNITS			
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	0.4113
Active Area Diameter	AA_{ϕ}			75			120			300			400			500		μm
Responsivity		λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
	R _λ	λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	C _j	V _R = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_R = 5.0V,$ $R_L = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Reverse Voltage					20			20			15			15			15	V
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz